

COMPARISON TABLE

■ FOR POWER MEASUREMENTS

MODEL		P _{MAX}	NOISE LEVEL	λ _{MIN}	λ _{MAX}	SENSOR TYPE	APERTURE	SEE PAGE
PH100-SiUV		4 mW	10 pW	210 nm	1.08 μm	UV-Silicon	10 mm Ø	118
PH100-SiUV-OD.3		11 mW	30 pW	210 nm	1.08 μm	UV-Silicon	10 mm Ø	118
PH100-SiUV-OD1		38 mW	100 pW	400 nm	1.08 μm	UV-Silicon	10 mm Ø	118
PH20-Ge		30 mW	60 pW	800 nm	1.65 μm	Germanium	5 mm Ø	118
PH100-Si-HA		36 mW	10 pW	350 nm	1.08 μm	Silicon	10 mm Ø	118
PH100-Si-HA-OD1		300 mW	100 pW	420 nm	1.08 μm	Silicon	10 mm Ø	118
PH20-Ge-OD1		300 mW	600 pW	900 nm	1.65 μm	Germanium	5 mm Ø	118
PH20-Ge-OD2		500 mW	6 nW	950 nm	1.65 μm	Germanium	5 mm Ø	118
PH100-Si-HA-OD2		750 mW	1 nW	630 nm	1.1 μm	Silicon	10 mm Ø	118
PRONTO-Si		800 mW	10 pW	320 nm	1.1 μm	Silicon	10 X 10 mm	124

FOR ENERGY MEASUREMENTS

MODEL		E _{MAX}	NOISE LEVEL	λ _{MIN}	λ _{MAX}	SENSOR TYPE	APERTURE	SEE PAGE
PE3B-Si		30 pJ	8 fJ	210 nm	1.08 μm	UV-Silicon	3 mm Ø	120
PE3B-In		300 pJ	30 fJ	900 nm	1.7 μm	InGaAs	3 mm Ø	120
PE5B-Ge		3 nJ	1 pJ	800 nm	1.65 μm	Germanium	5 mm Ø	120
PE10B-Si		150 nJ	1.5 pJ	210 nm	1.08 μm	UV-Silicon	10 mm Ø	120

 Available with INTEGRA all-in-one detector + meter

